

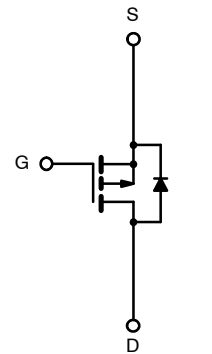
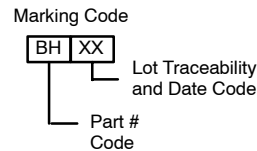
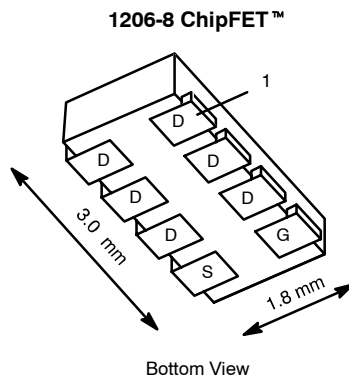


P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-30	0.085 @ $V_{GS} = -4.5$ V	-4.3
	0.135 @ $V_{GS} = -2.5$ V	-3.4

TrenchFET®
Power MOSFETs
2.5-V Rated



P-Channel MOSFET

Ordering Information: Si5449DC-T1

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	5 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	-30		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	-4.3	-3.1	A
	T _A = 85°C		-3.1	-2.2	
Pulsed Drain Current		I _{DM}	-15		
Continuous Source Current ^a		I _{AS}	-2.1	-1.1	
Maximum Power Dissipation ^a	T _A = 25°C	P _D	2.5	1.3	W
	T _A = 85°C		1.3	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	40	50	$^\circ\text{C/W}$
	Steady State		80	95	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	15	20	

Notes

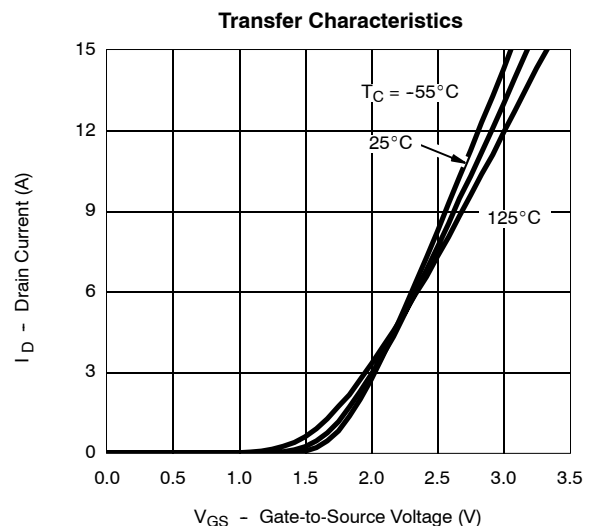
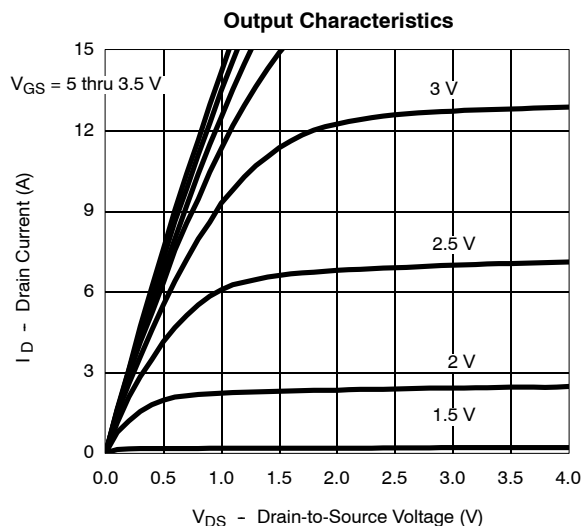
- Surface Mounted on 1" x 1" FR4 Board.
- See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.6			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 12\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24\ \text{V}, V_{GS} = 0\ \text{V}$			-1	μA
		$V_{DS} = -24\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\ \text{V}, V_{GS} = -4.5\ \text{V}$	-15			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\ \text{V}, I_D = -3.1\ \text{A}$		0.071	0.085	Ω
		$V_{GS} = -2.5\ \text{V}, I_D = -1\ \text{A}$		0.112	0.135	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\ \text{V}, I_D = -3.1\ \text{A}$		8.5		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.1\ \text{A}, V_{GS} = 0\ \text{V}$		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -15\ \text{V}, V_{GS} = -4.5\ \text{V}, I_D = -3.1\ \text{A}$		7.2	11	nC
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			1.7		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\ \text{V}, R_L = 15\ \Omega$ $I_D \cong -1\ \text{A}, V_{GEN} = -4.5\ \text{V}, R_G = 6\ \Omega$		13	25	μs
Rise Time	t_r			14	30	
Turn-Off Delay Time	$t_{d(off)}$			35	70	
Fall Time	t_f			20	40	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.1\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		40	60	ns

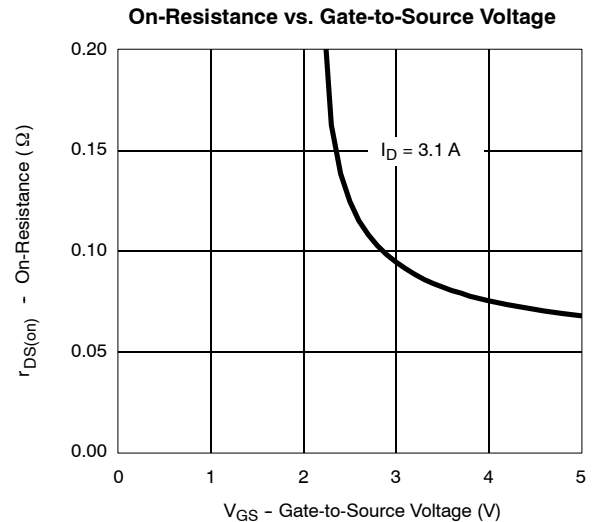
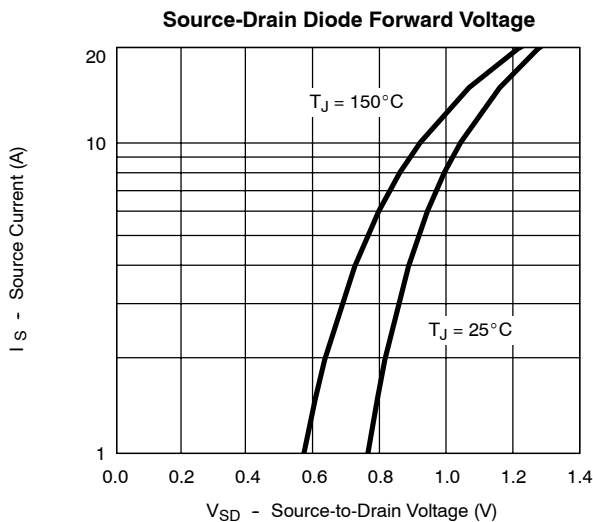
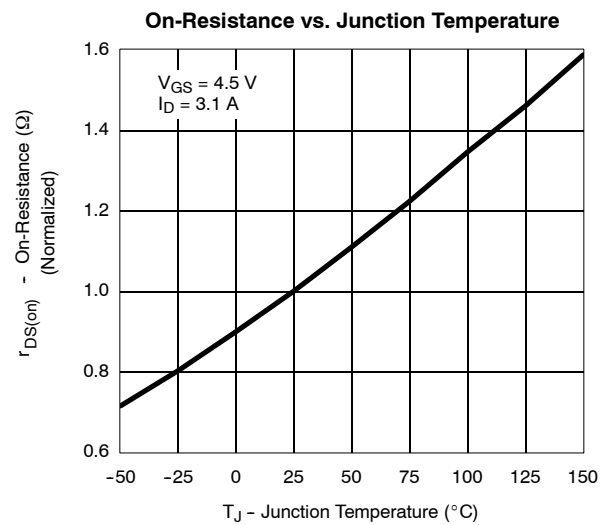
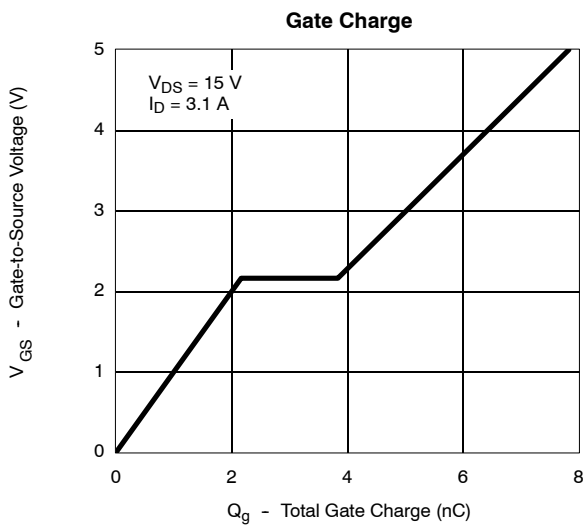
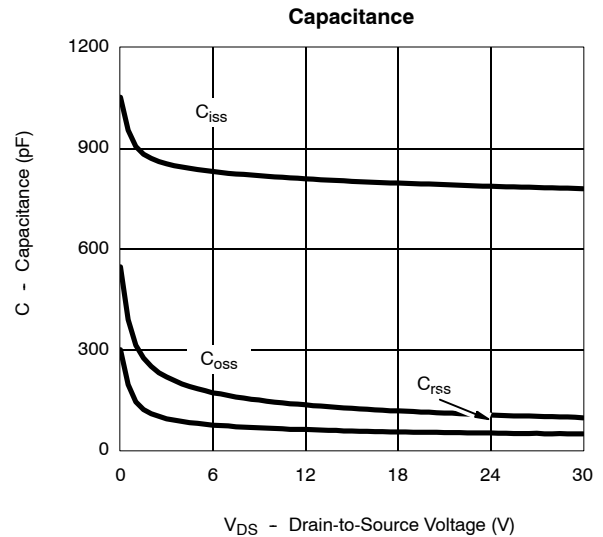
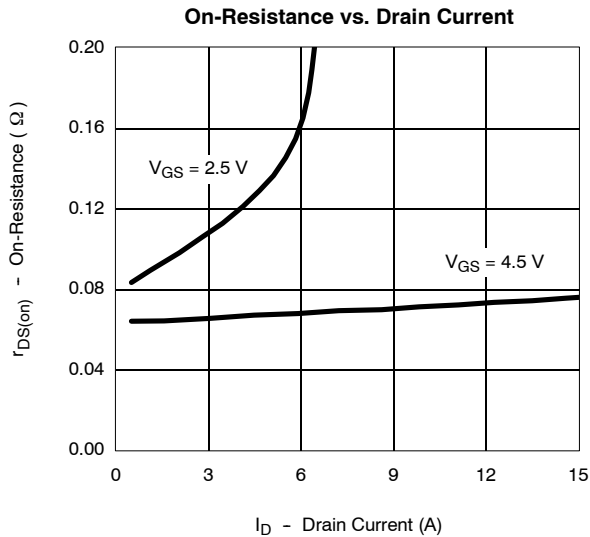
Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)
